



#9/B
2-11-03
Mullish

THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of:

YASUMOTO, Tamihide

Group Art Unit: 2813

Serial No.: 09/995,575

Examiner: **KIELIN, E.**

Filed: **November 29, 2001**

P.T.O. Confirmation No.: 1497

For: **SEMICONDUCTOR DEVICE MANUFACTURING METHOD USING METAL SILICIDE REACTION AFTER ION IMPLANTATION IN SILICON WIRING**

AMENDMENT

Commissioner for Patents
Washington, D.C. 20231

February 5, 2003

Sir:

In response to the Office Action dated September 24, 2002, please amend the above-identified application as follows:

IN THE CLAIMS:

Please **AMEND** claims 1 and 5 as follows:

RECEIVED
FEB 10 2003
TECHNOLOGY CENTER 2800

-
- 1 1. (Twice Amended) A method for manufacturing a semiconductor device, comprising the steps
- 2 of:
- 3 **B'** forming a wiring comprising silicon on a surface of a semiconductor substrate;
- 4 covering part of the wiring with a resist pattern;
- 5 implanting arsenic ions into the wiring using the resist pattern as a mask;
- 6 removing the resist pattern;